

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

Instead of http://www.nxp.com, http://www.nxp.com, http://www.nexperia.com, http://www.nexperia.com,

Instead of sales.addresses@www.nxp.com or sales.addresses@www.semiconductors.philips.com, use salesaddresses@nexperia.com (email)

Replace the copyright notice at the bottom of each page or elsewhere in the document, depending on the version, as shown below:

- © NXP N.V. (year). All rights reserved or © Koninklijke Philips Electronics N.V. (year). All rights reserved

Should be replaced with:

- © Nexperia B.V. (year). All rights reserved.

If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

74AHC32; 74AHCT32

Quad 2-input OR gate Rev. 04 — 22 May 2008

Product data sheet

General description 1.

The 74AHC32; 74AHCT32 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7-A.

The 74AHC32; 74AHCT32 provides the 2-input OR function.

Features 2.

- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than V_{CC}
- Input levels:
 - ◆ For 74AHC32: CMOS level
 - ◆ For 74AHCT32: TTL level
- ESD protection:
 - ◆ HBM EIA/JESD22-A114E exceeds 2000 V
 - MM EIA/JESD22-A115-A exceeds 200 V
 - ◆ CDM EIA/JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

Ordering information 3.

Table 1. **Ordering information**

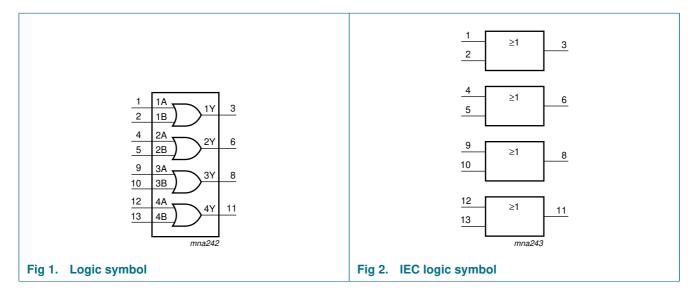
Type number	Package								
	Temperature range	Name	Description	Version					
74AHC32	'	'		'					
74AHC32D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1					
74AHC32PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1					
74AHC32BQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5\times3\times0.85$ mm	SOT762-1					

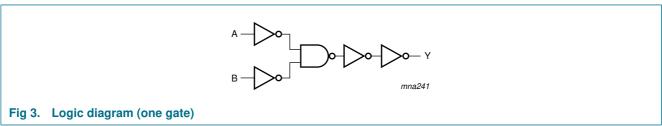


 Table 1.
 Ordering information ...continued

Type number	Package								
	Temperature range	Name	Description	Version					
74AHCT32									
74AHCT32D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1					
74AHCT32PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1					
74AHCT32BQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5\times3\times0.85$ mm	SOT762-1					

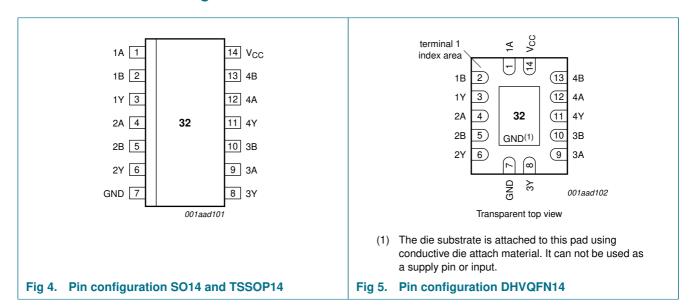
4. Functional diagram





5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A	1	data input
1B	2	data input
1Y	3	data output
2A	4	data input
2B	5	data input
2Y	6	data output
GND	7	ground (0 V)
3Y	8	data output
3A	9	data input
3B	10	data input
4Y	11	data output
4A	12	data input
4B	13	data input
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function table [1]

Input	Output	
nA	nB	nY
L	L	L
X	Н	Н
Н	X	Н

^[1] H = HIGH voltage level;

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

		<i>y</i> , , , , , , , , , , , , , , , , , , ,			,
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_1 < -0.5 \text{ V}$	<u>[1]</u> –20	-	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> –20	+20	mA
lo	output current	$V_O = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	-25	+25	mA
I _{CC}	supply current		-	+75	mA
I _{GND}	ground current		–75	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	500	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

8. Recommended operating conditions

Table 5. Operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
74AHC3	32					
V_{CC}	supply voltage		2.0	5.0	5.5	V
VI	input voltage		0	-	5.5	V
V _O	output voltage		0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	100	ns/V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	20	ns/V

L = LOW voltage level;

X = don't care.

^[2] For SO14 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K. For TSSOP14 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K. For DHVQFN14 packages: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

 Table 5.
 Operating conditions ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
74AHCT	32					
V _{CC}	supply voltage		4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	20	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74AHC3	2	•	•		1				'	
V _{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 3.0 \text{ V}$	2.1	-	-	2.1	-	2.1	-	V
		$V_{CC} = 5.5 \text{ V}$	3.85	-	-	3.85	-	3.85	-	V
V_{IL}	LOW-level	$V_{CC} = 2.0 \text{ V}$	-	-	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V _{OH} HIGH-leve	HIGH-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = -50 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -50 \ \mu A; \ V_{CC} = 3.0 \ V$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_O = -50 \ \mu A; \ V_{CC} = 4.5 \ V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_O = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.80	-	3.70	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 50 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \ \mu A; \ V_{CC} = 3.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		$I_{O} = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
l _l	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	0.1	-	1.0	-	2.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	2.0	-	20	-	40	μΑ
C _I	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF
Co	output capacitance		-	4	-	-	-	-	-	pF

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74AHCT	32									
V _{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	0.8	-	0.8	-	8.0	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_O = -50 \mu A$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -8.0 \text{ mA}$	3.94	-	-	3.80	-	3.70	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	Ι _Ο = 50 μΑ	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 8.0 \text{ mA}$	-	-	0.36	-	0.44	-	0.55	V
II	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	2.0	-	20	-	40	μΑ
Δl _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}$; other pins at V_{CC} or GND; $I_O = 0 \text{ A}$; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
Cı	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF
Co	output capacitance		-	4	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

J		10									
Symbol	Parameter	Conditions			25 °C –		–40 °C t	o +85 °C	-40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	Min	Max	1
74AHC3	2				•	•					
t _{pd}	propagation	nA, nB to nY; see Figure 6	[2]								
	delay	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$									
		C _L = 15 pF		-	3.9	7.9	1.0	9.5	1.0	10.0	ns
		C _L = 50 pF		-	5.6	11.4	1.0	13	1.0	14.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		C _L = 15 pF		-	2.8	5.5	1.0	6.5	1.0	7.0	ns
		C _L = 50 pF		-	4.1	7.5	1.0	8.5	1.0	9.5	ns
C_{PD}	power dissipation capacitance	$f_i = 1$ MHz; $V_I = GND$ to V_{CC}	[3]	-	10	-	-	-	-	-	pF

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

Symbol	Parameter	Conditions		25 °C -		–40 °C to	+85 °C	–40 °C to	Unit		
				Min	Typ[1]	Max	Min	Max	Min	Max	
74AHCT32; V _{CC} = 4.5 V to 5.5 V									'		
t _{pd}		nA, nB to nY; see Figure 6	[2]								
	delay	C _L = 15 pF		-	3.1	6.9	1.0	8.0	1.0	9.0	ns
		C _L = 50 pF		-	4.3	7.9	1.0	9.0	1.0	10.0	ns
C _{PD}	power dissipation capacitance	f_i = 1 MHz; V_I = GND to V_{CC}	[3]	-	12	-	-	-	-	-	pF

- [1] Typical values are measured at nominal supply voltage ($V_{CC} = 3.3 \text{ V}$ and $V_{CC} = 5.0 \text{ V}$).
- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

11. Waveforms

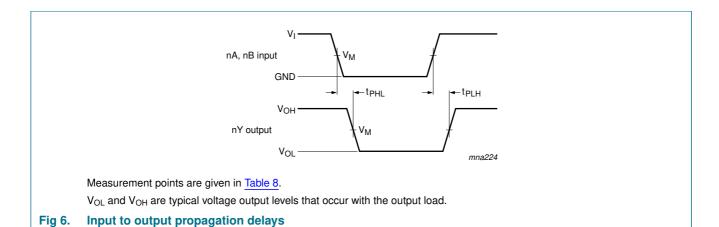
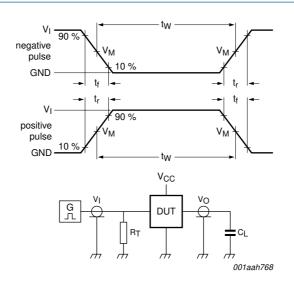


Table 8. Measurement points

Туре	Input	Output		
	V _M	V_{M}		
74AHC32	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$		
74AHCT32	1.5 V	$0.5 \times V_{CC}$		

8 of 14



Test data is given in Table 9.

Definitions test circuit:

 R_T = termination resistance should be equal to output impedance Z_o of the pulse generator.

 C_L = load capacitance including jig and probe capacitance.

Fig 7. Load circuitry for measuring switching times

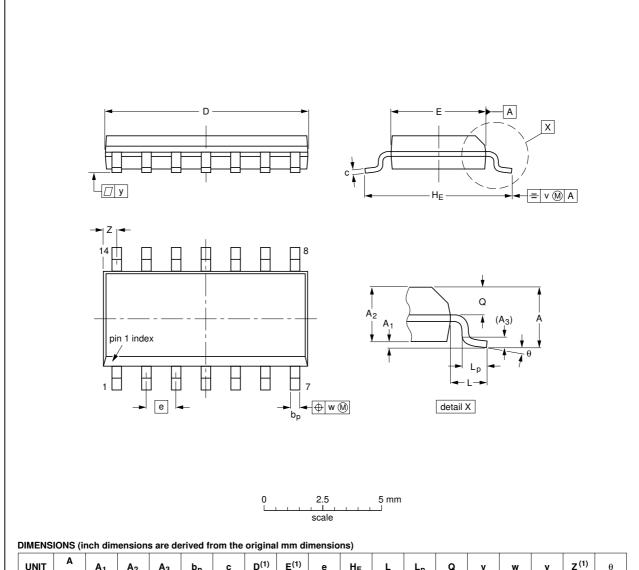
Table 9. Test data

Туре	Input		Load	Test
	VI	t _r , t _f	CL	
74AHC32	V _{CC}	≤ 3.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}
74AHCT32	3.0 V	≤ 3.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}

12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

Note

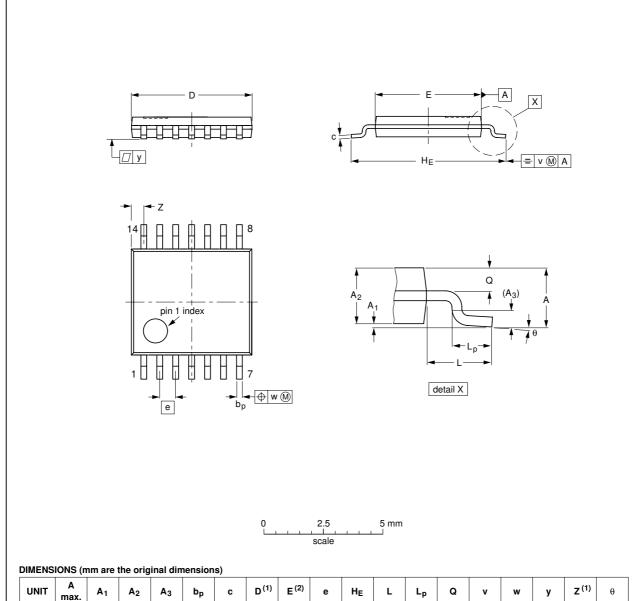
1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT108-1	076E06	MS-012				99-12-27 03-02-19

Fig 8. Package outline SOT108-1 (SO14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT402-1		MO-153				99-12-27 03-02-18	

Fig 9. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

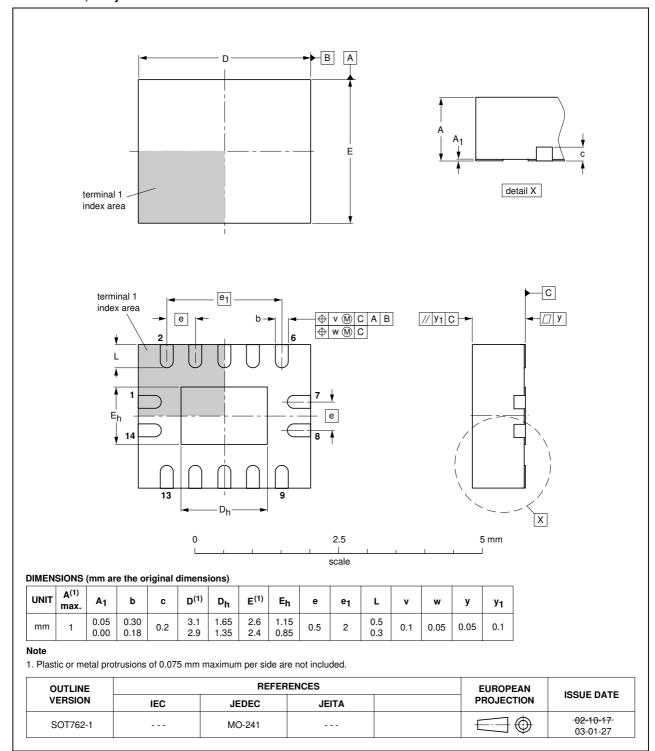


Fig 10. Package outline SOT762-1 (DHVQFN14)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
74AHC_AHCT32_4	20080522	Product data sheet	-	74AHC_AHCT32_3			
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidel of NXP Semiconductors. 						
	 Legal texts ha 	ive been adapted to the new c	ompany name where	appropriate.			
	• <u>Table 6</u> : the co	onditions for input leakage cur	rent have been chang	ed.			
74AHC_AHCT32_3	20040519	Product specification	-	74AHC_AHCT32_2			
74AHC_AHCT32_2	19990927	Product specification	-	74AHC_AHCT32_1			
74AHC_AHCT32_1	19981209	Preliminary specification	-	-			
		·		·			

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

15.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

15.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or

malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

15.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

16. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

17. Contents

1	General description
2	Features 1
3	Ordering information
4	Functional diagram
5	Pinning information
5.1	Pinning
5.2	Pin description
6	Functional description
7	Limiting values
8	Recommended operating conditions
9	Static characteristics
10	Dynamic characteristics
11	Waveforms
12	Package outline 9
13	Abbreviations
14	Revision history
15	Legal information
15.1	Data sheet status
15.2	Definitions
15.3	Disclaimers
15.4	Trademarks13
16	Contact information
17	Contents 1/

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

